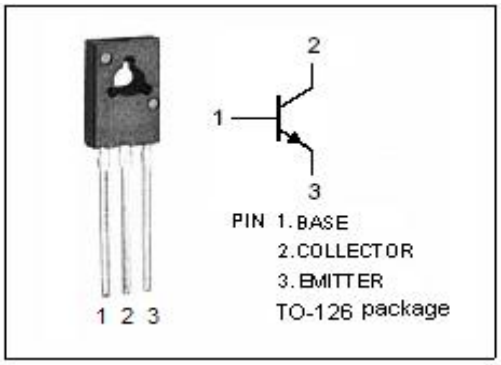
isc Silicon NPN Power Transistor 2SC2899

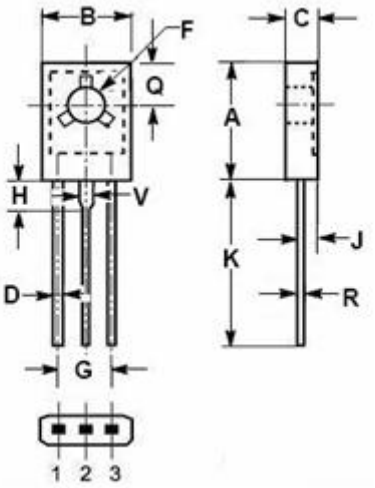


DESCRIPTION

- Collector–Emitter Sustaining Voltage
  : $V_{CEO(SUS)}$ = 400V(Min.)
- Collector Saturation Voltage
  : $V_{CE(sat)}$ = 1.0(Max) @ I_C= 0.25A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for use in high-voltage, high-speed, power switching in inductive circuit, they are particularly suited for 115 and 220V switchmode applications such as switching regulators, inverters, DC-DC converter, Motor control, Solenoid/Relay drivers and deflection circuits.



DIM	mm MIN	MAX
A	10.70	10.95
B	7.70	7.90
C	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
H	2.00	2.20
J	1.35	1.55
K	15.30	16.30
Q	3.70	3.90
R	0.40	0.60
V	1.17	1.37

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector- Base Voltage	500	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	10	V
I_C	Collector Current-Continuous	0.5	A
I_{CM}	Collector Current-peak	1.0	A
P_C	Collector Power Dissipation T_a=25℃	0.75	W
	Collector Power Dissipation T_C=25℃	10	
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C =25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 50mA; I_B= 0	400			V
$V_{(BR)EBO}$	Emitter to base breakdown voltage	I_E = 10 mA, I_C = 0	10			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 0.25 A ;I_B= 0.05A			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 0.25 A ;I_B= 0.05A			1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 400V;I_E= 0			20	uA
I_{CEO}	Collector Cutoff Current	V_{CE}= 350V; R_{BE} = ∞			50	uA
h_{FE-1}	DC Current Gain	I_C= 0.25 A; V_{CE}= 5V	15			
h_{FE-2}	DC Current Gain	I_C= 0.5A; V_{CE}=5V	7			